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## MOSFET

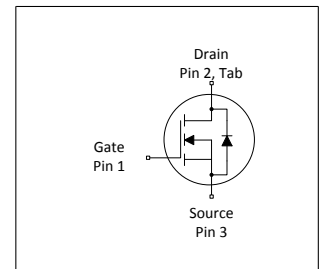
### 600V CoolMOS™ P7 Power Transistor

The CoolMOS™ 7th generation platform is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. The 600V CoolMOS™ P7 series is the successor to the CoolMOS™ P6 series. It combines the benefits of a fast switching SJ MOSFET with excellent ease of use, e.g. very low ringing tendency, outstanding robustness of body diode against hard commutation and excellent ESD capability. Furthermore, extremely low switching and conduction losses make switching applications even more efficient, more compact and much cooler.



### Features

- Suitable for hard and soft switching (PFC and LLC) due to an outstanding commutation ruggedness
- Significant reduction of switching and conduction losses
- Excellent ESD robustness >2kV (HBM) for all products
- Better  $R_{DS(on)}/package$  products compared to competition enabled by a low  $R_{DS(on)} \cdot A$  (below  $10\text{Ohm} \cdot \text{mm}^2$ )
- Fully qualified acc. JEDEC for Industrial Applications



### Benefits

- Ease of use and fast design-in through low ringing tendency and usage across PFC and PWM stages
- Simplified thermal management due to low switching and conduction losses
- Increased power density solutions enabled by using products with smaller footprint and higher manufacturing quality due to >2 kV ESD protection
- Suitable for a wide variety of applications and power ranges



### Potential applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	99	$\text{m}\Omega$
$Q_{g,typ}$	45	nC
$I_{D,pulse}$	100	A
$E_{oss} @ 400V$	5.0	$\mu\text{J}$
Body diode $di_f/dt$	900	$\text{A}/\mu\text{s}$

Type / Ordering Code	Package	Marking	Related Links
IPW60R099P7	PG-TO 247-3	60R099P7	see Appendix A

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## 1 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	31 20	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	100	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	105	mJ	$I_D=5.1\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10
Avalanche energy, repetitive	$E_{AR}$	-	-	0.53	mJ	$I_D=5.1\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10
Avalanche current, single pulse	$I_{AS}$	-	-	5.1	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	80	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	$V_{GS}$	-20	-	20	V	static;
Gate source voltage (dynamic)	$V_{GS}$	-30	-	30	V	AC ( $f>1\text{ Hz}$ )
Power dissipation	$P_{tot}$	-	-	117	W	$T_C=25^\circ\text{C}$
Storage temperature	$T_{stg}$	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	$T_j$	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	60	Ncm	M3 and M3.5 screws
Continuous diode forward current	$I_S$	-	-	31	A	$T_C=25^\circ\text{C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	100	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	50	V/ns	$V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 31\text{A}$ , $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di <sub>F</sub> /dt	-	-	900	A/ $\mu\text{s}$	$V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 31\text{A}$ , $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	$V_{ISO}$	-	-	n.a.	V	$V_{rms}$ , $T_C=25^\circ\text{C}$ , $t=1\text{min}$

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum Duty Cycle  $D = 0.50$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_\theta$

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.07	°C/W	-
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62	°C/W	leaded
Thermal resistance, junction - ambient for SMD version	$R_{thJA}$	-	-	-	°C/W	-
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

### 3 Electrical characteristics

at  $T_j=25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{V}$ , $I_D=1\text{mA}$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$ , $I_D=0.53\text{mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=25^\circ\text{C}$ $V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=150^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{V}$ , $V_{DS}=0\text{V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.077 0.180	0.099	$\Omega$	$V_{GS}=10\text{V}$ , $I_D=10.5\text{A}$ , $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$ , $I_D=10.5\text{A}$ , $T_j=150^\circ\text{C}$
Gate resistance	$R_G$	-	5.9	-	$\Omega$	$f=1\text{MHz}$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	1952	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=400\text{V}$ , $f=250\text{kHz}$
Output capacitance	$C_{oss}$	-	33	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=400\text{V}$ , $f=250\text{kHz}$
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	62	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=0\dots400\text{V}$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	649	-	pF	$I_D=\text{constant}$ , $V_{GS}=0\text{V}$ , $V_{DS}=0\dots400\text{V}$
Turn-on delay time	$t_{d(on)}$	-	23	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=10.5\text{A}$ , $R_G=5.3\Omega$ ; see table 9
Rise time	$t_r$	-	15	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=10.5\text{A}$ , $R_G=5.3\Omega$ ; see table 9
Turn-off delay time	$t_{d(off)}$	-	89	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=10.5\text{A}$ , $R_G=5.3\Omega$ ; see table 9
Fall time	$t_f$	-	5	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=10.5\text{A}$ , $R_G=5.3\Omega$ ; see table 9

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	11	-	nC	$V_{DD}=400\text{V}$ , $I_D=10.5\text{A}$ , $V_{GS}=0$ to $10\text{V}$
Gate to drain charge	$Q_{gd}$	-	13	-	nC	$V_{DD}=400\text{V}$ , $I_D=10.5\text{A}$ , $V_{GS}=0$ to $10\text{V}$
Gate charge total	$Q_g$	-	45	-	nC	$V_{DD}=400\text{V}$ , $I_D=10.5\text{A}$ , $V_{GS}=0$ to $10\text{V}$
Gate plateau voltage	$V_{plateau}$	-	5.2	-	V	$V_{DD}=400\text{V}$ , $I_D=10.5\text{A}$ , $V_{GS}=0$ to $10\text{V}$

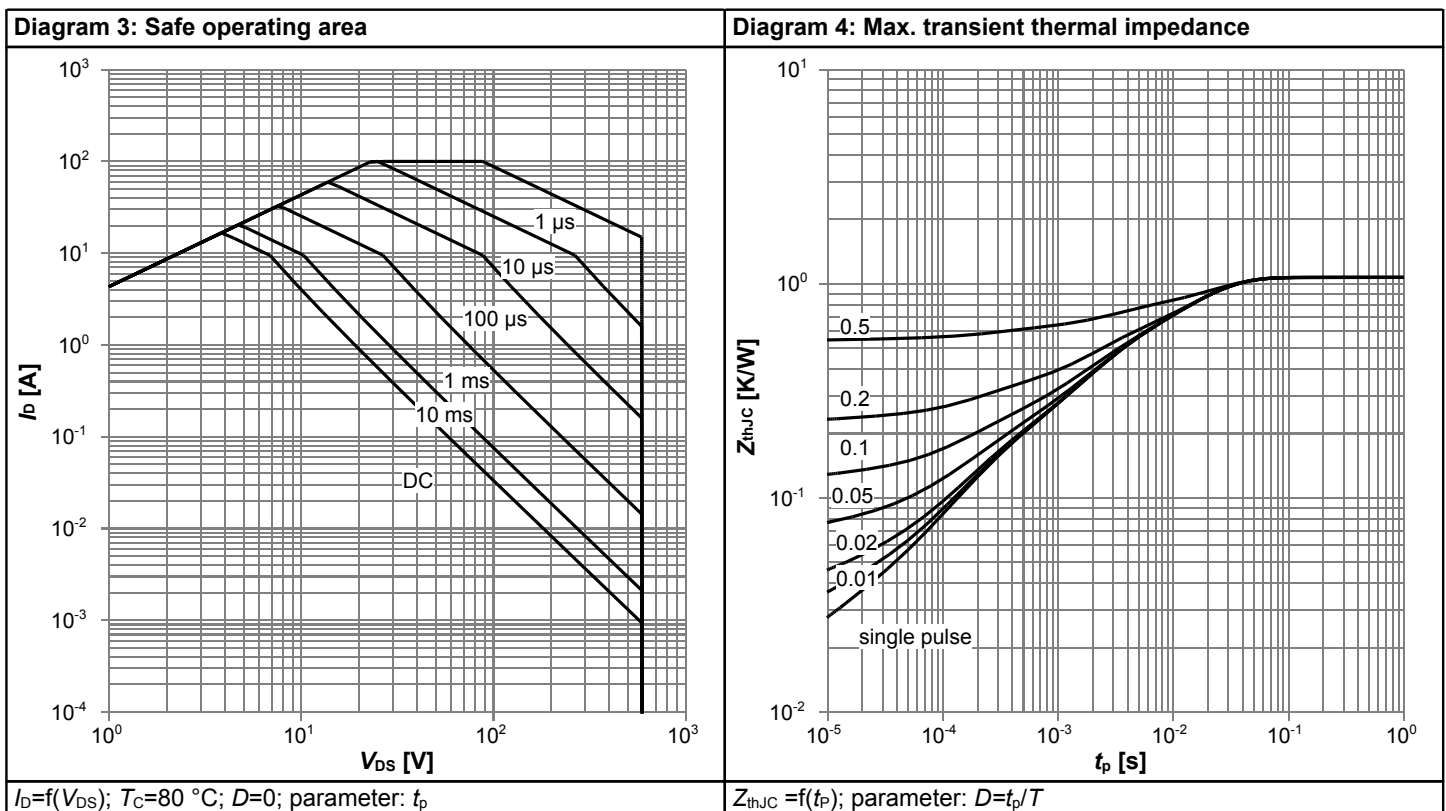
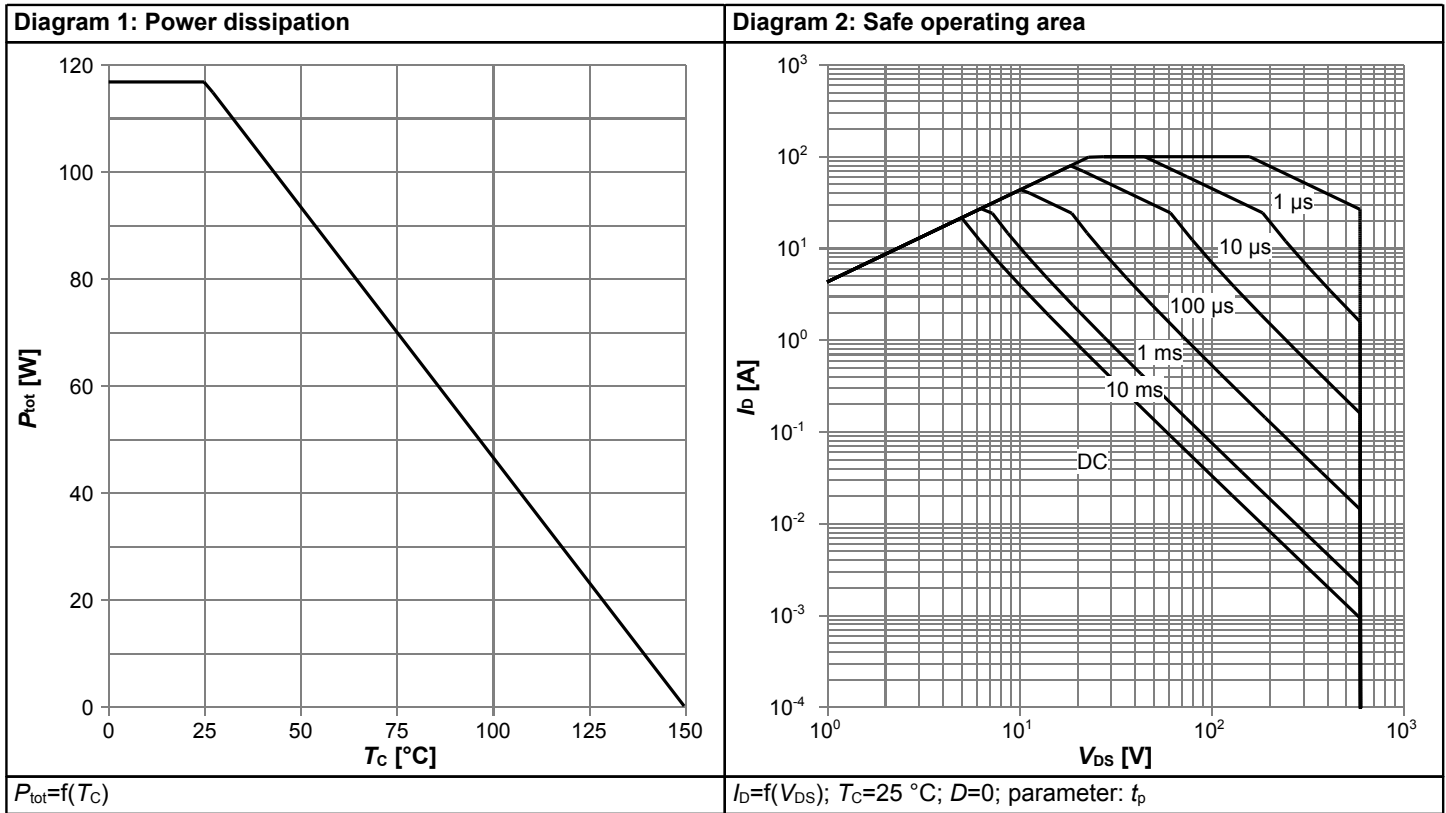
<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

**Table 7 Reverse diode characteristics**

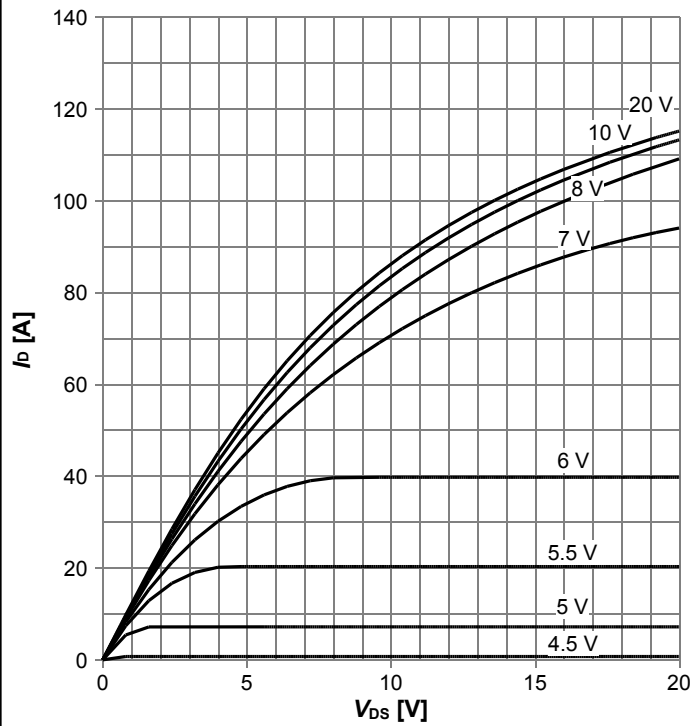
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0V, I_F=10.5A, T_j=25^{\circ}C$
Reverse recovery time	$t_{rr}$	-	211	-	ns	$V_R=400V, I_F=4A, di_F/dt=100A/\mu s$ ; see table 8
Reverse recovery charge	$Q_{rr}$	-	2.1	-	$\mu C$	$V_R=400V, I_F=4A, di_F/dt=100A/\mu s$ ; see table 8
Peak reverse recovery current	$I_{rrm}$	-	20.1	-	A	$V_R=400V, I_F=4A, di_F/dt=100A/\mu s$ ; see table 8

### 4 Electrical characteristics diagrams



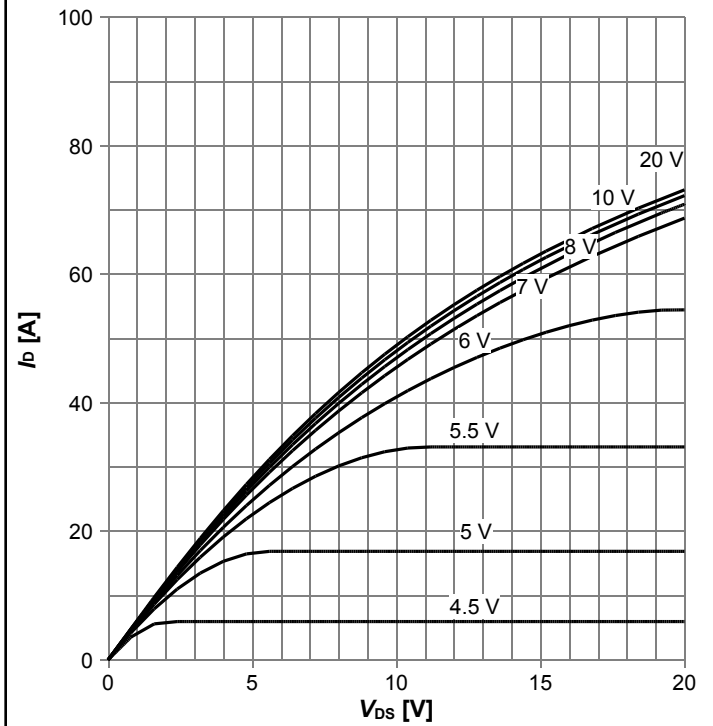


**Diagram 5: Typ. output characteristics**



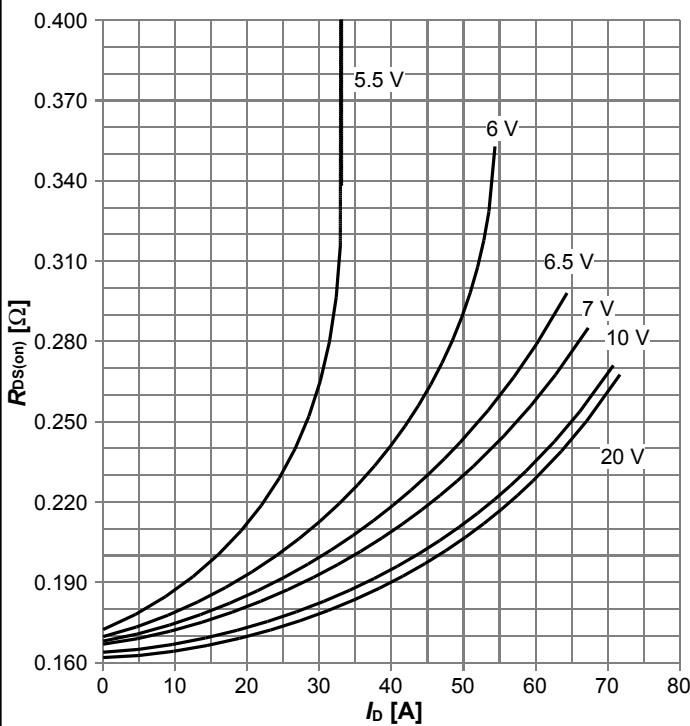
$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$

**Diagram 6: Typ. output characteristics**



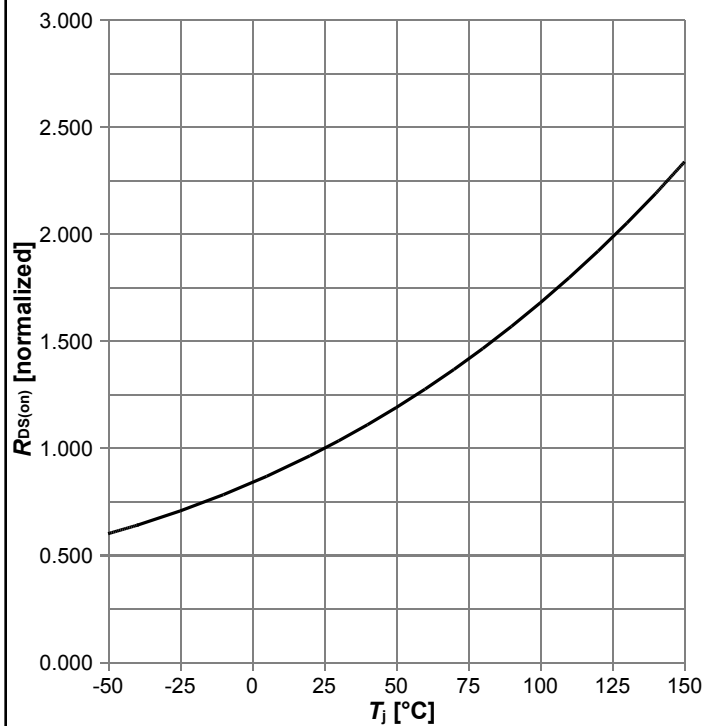
$I_D=f(V_{DS}); T_j=125\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$

**Diagram 7: Typ. drain-source on-state resistance**



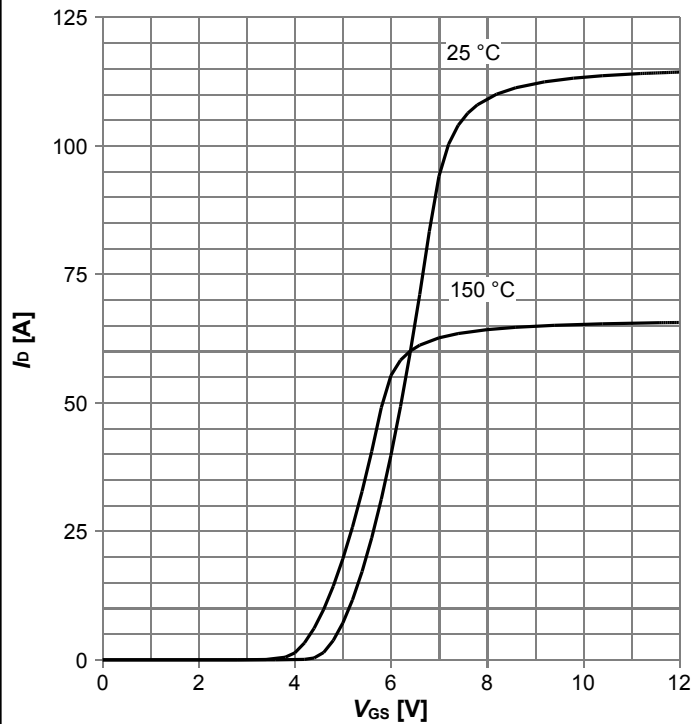
$R_{DS(on)}=f(I_D); T_j=125\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$

**Diagram 8: Drain-source on-state resistance**



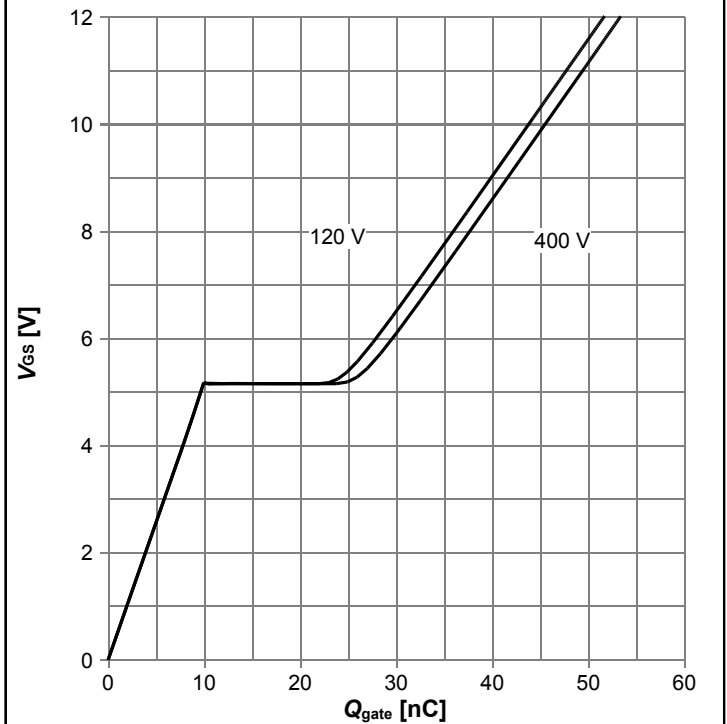
$R_{DS(on)}=f(T_j); I_D=10.5\text{ A}; V_{GS}=10\text{ V}$

**Diagram 9: Typ. transfer characteristics**



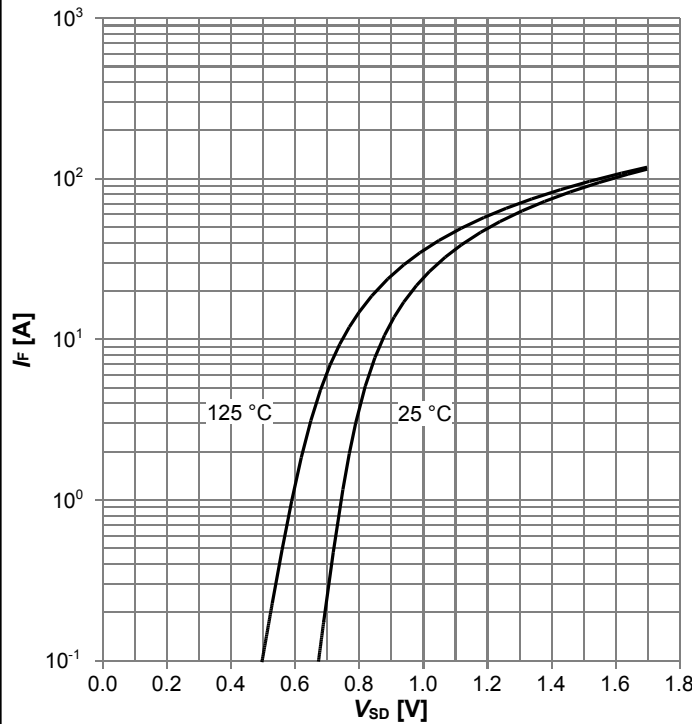
$I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

**Diagram 10: Typ. gate charge**



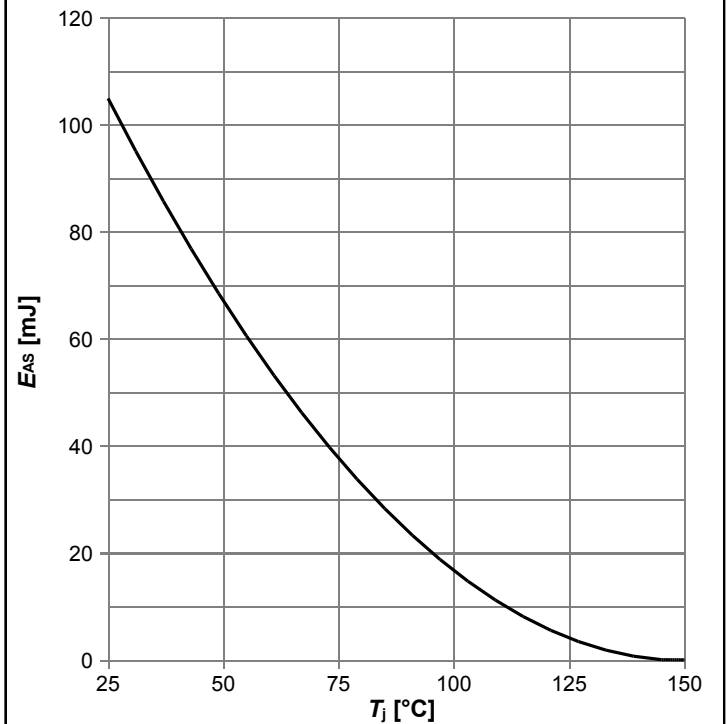
$V_{GS} = f(Q_{gate}); I_D = 10.5 \text{ A pulsed}; \text{parameter: } V_{DD}$

**Diagram 11: Forward characteristics of reverse diode**



$I_F = f(V_{SD}); \text{parameter: } T_j$

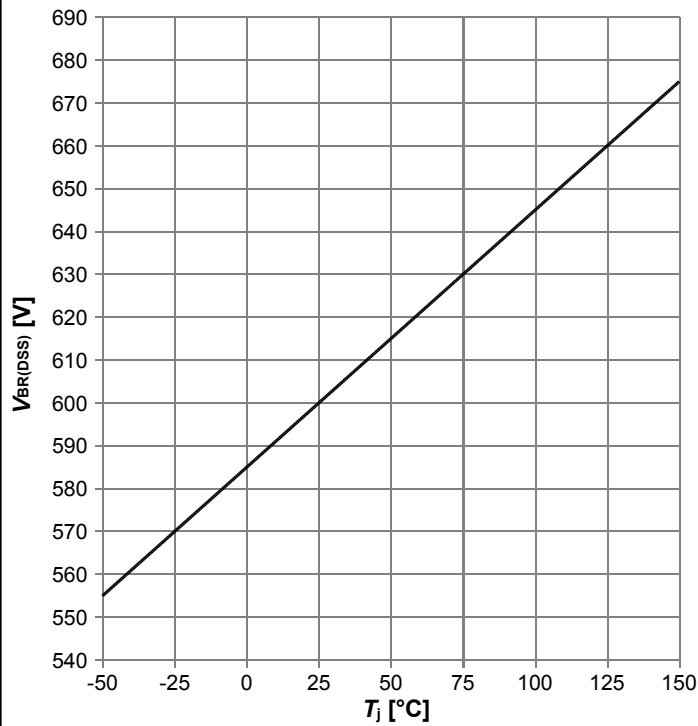
**Diagram 12: Avalanche energy**



$E_{AS} = f(T_j); I_D = 5.1 \text{ A}; V_{DD} = 50 \text{ V}$

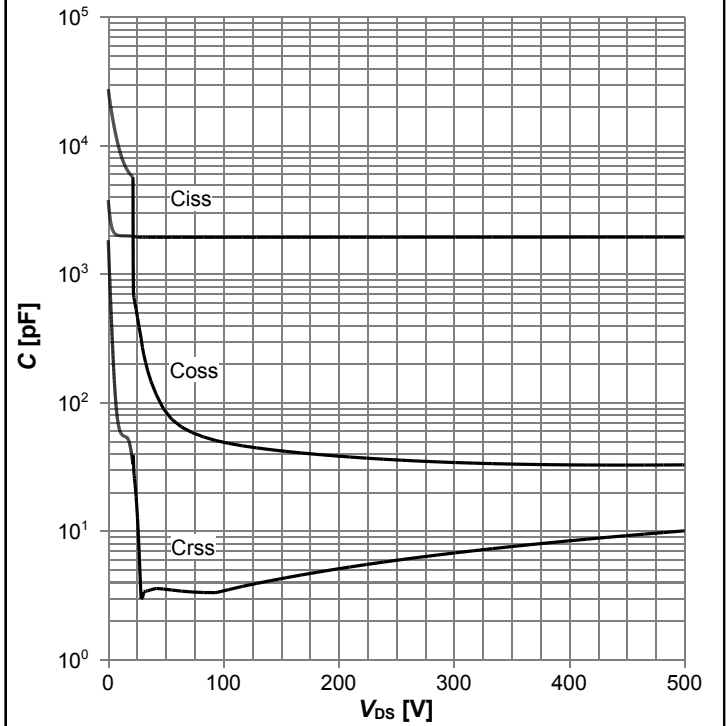
**600V CoolMOS™ P7 Power Transistor**  
**IPW60R099P7**

**Diagram 13: Drain-source breakdown voltage**



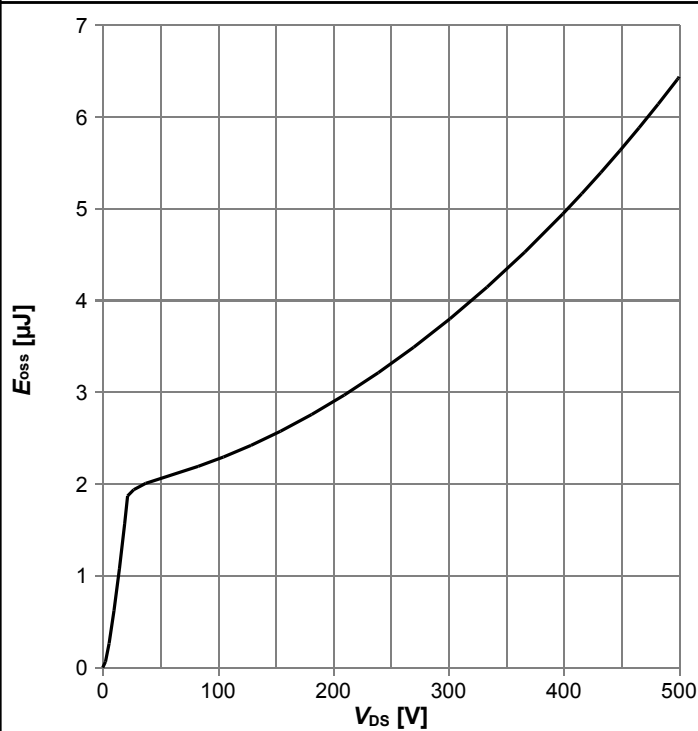
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

**Diagram 14: Typ. capacitances**



$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=250 \text{ kHz}$

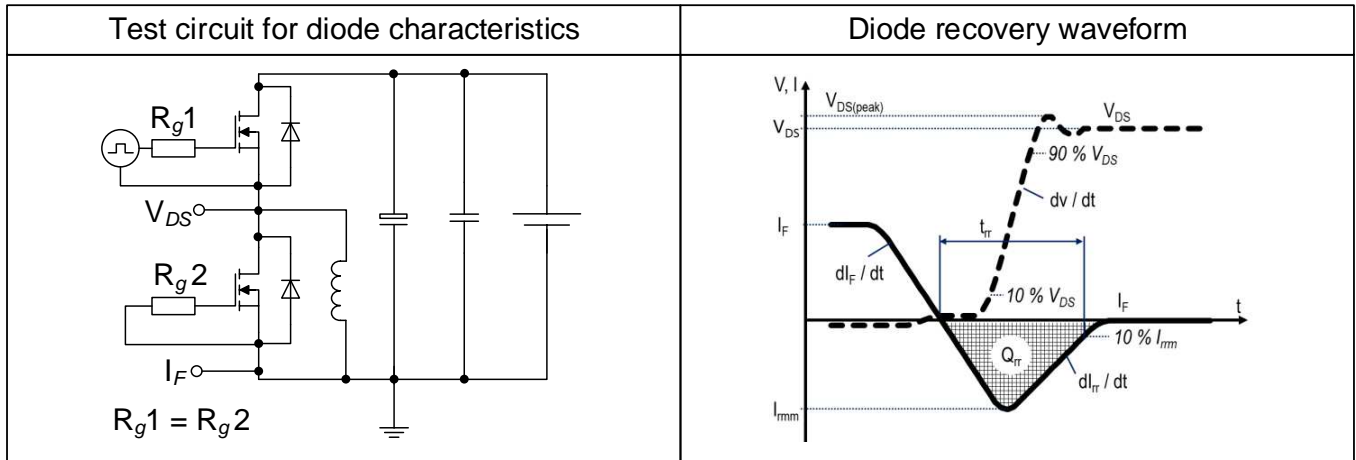
**Diagram 15: Typ. Coss stored energy**



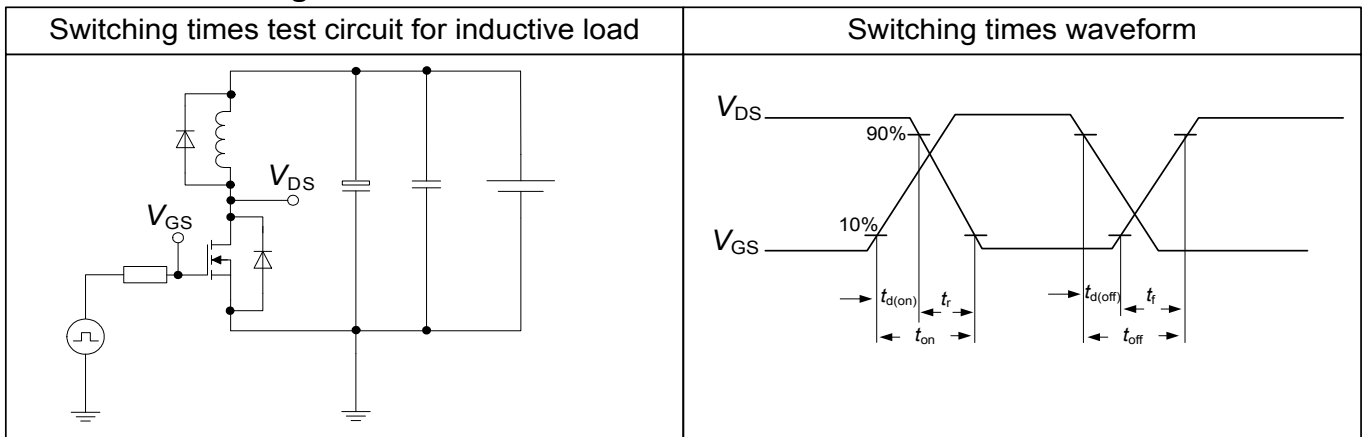
$E_{oss}=f(V_{DS})$

## 5 Test Circuits

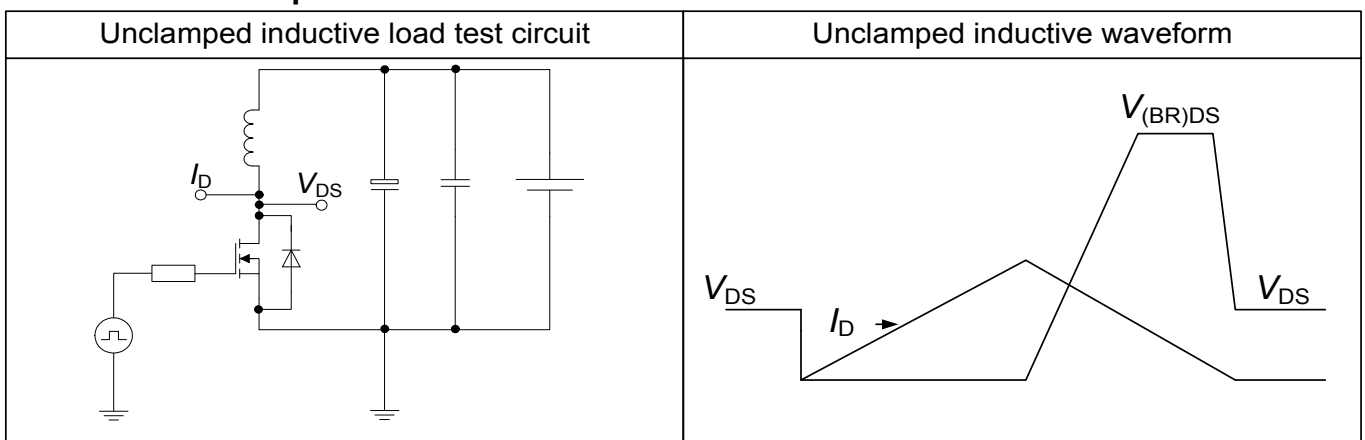
**Table 8 Diode characteristics**



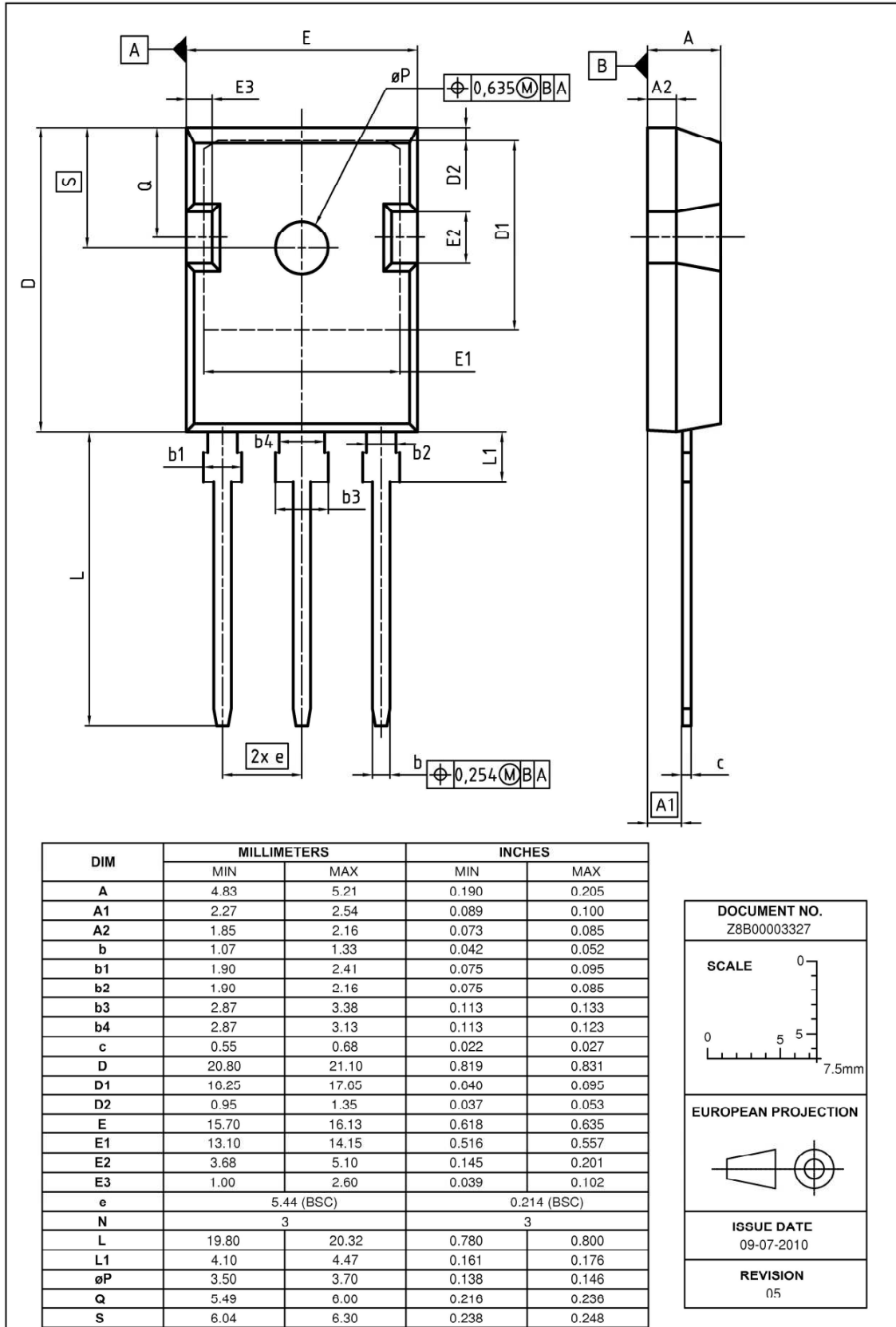
**Table 9 Switching times**



**Table 10 Unclamped inductive load**



**6 Package Outlines**



**Figure 1 Outline PG-TO 247-3, dimensions in mm/inches**

## 7 Appendix A

### Table 11 Related Links

- IFX CoolMOS P7 Webpage: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS P7 application note: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS P7 simulation model: [www.infineon.com](http://www.infineon.com)
- IFX Design tools: [www.infineon.com](http://www.infineon.com)

## Revision History

IPW60R099P7

**Revision: 2018-05-15, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2017-05-18	Release of final version
2.1	2018-05-15	Updated diagram scalings; Nomenclature of product qualification grade was changed

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